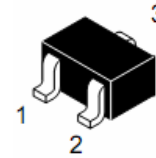


WNM2025

Single N-Channel, 20V, 3.9 A, Power MOSFET

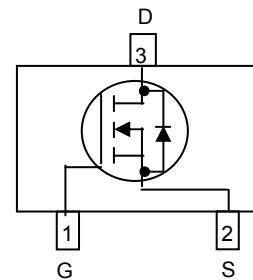
V _{DS} (V)	R _{ds(on)} (Ω)
20	0.027@ V _{GS} =4.5V
	0.031@ V _{GS} =2.5V
	0.036@ V _{GS} =1.8V



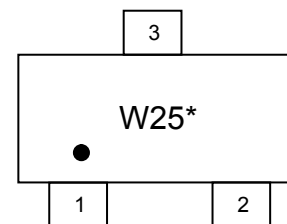
SOT-23-3L

Descriptions

The WNM2025 is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent R_{DS (ON)} with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product WNM2025 is Pb-free.



Pin configuration (Top view)



W25= Device Code
* = Month (A~Z)

Marking

Features

- Trench Technology
- Supper high density cell design
- Excellent ON resistance for higher DC current
- Extremely Low Threshold Voltage
- Small package SOT-23-3L

Applications

- Driver for Relay, Solenoid, Motor, LED etc.
- DC-DC converter circuit
- Power Switch
- Load Switch
- Charging

Order information

Device	Package	Shipping
WNM2025-3/TR	SOT-23-3L	3000/Reel&Tape

WNM2025
Absolute Maximum ratings

Parameter		Symbol	10 S	Steady State	Unit
Drain-Source Voltage		V_{DS}	20		V
Gate-Source Voltage		V_{GS}	± 8		
Continuous Drain Current ^a	$T_A=25^\circ\text{C}$	I_D	3.9	3.6	A
	$T_A=70^\circ\text{C}$		3.1	2.9	
Maximum Power Dissipation ^a	$T_A=25^\circ\text{C}$	P_D	0.8	0.7	W
	$T_A=70^\circ\text{C}$		0.5	0.4	
Continuous Drain Current ^b	$T_A=25^\circ\text{C}$	I_D	3.6	3.3	A
	$T_A=70^\circ\text{C}$		2.8	2.6	
Maximum Power Dissipation ^b	$T_A=25^\circ\text{C}$	P_D	0.7	0.6	W
	$T_A=70^\circ\text{C}$		0.4	0.3	
Pulsed Drain Current ^c		I_{DM}	15		A
Operating Junction Temperature		T_J	150		$^\circ\text{C}$
Lead Temperature		T_L	260		$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-55 to 150		$^\circ\text{C}$

Thermal resistance ratings

Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance ^a	$t \leq 10 \text{ s}$	$R_{\theta JA}$	120	145	$^\circ\text{C}/\text{W}$
	Steady State		132	168	
Junction-to-Ambient Thermal Resistance ^b	$t \leq 10 \text{ s}$	$R_{\theta JA}$	145	174	
	Steady State		158	202	
Junction-to-Case Thermal Resistance		$R_{\theta JC}$	60	75	

a Surface mounted on FR4 Board using 1 square inch pad size, 1oz copper

b Surface mounted on FR4 board using minimum pad size, 1oz copper

c Repetitive rating, pulse width limited by junction temperature, $t_p=10\mu\text{s}$, Duty Cycle=1%

d Repetitive rating, pulse width limited by junction temperature $T_J=150^\circ\text{C}$.



WNM2025

Electronics Characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _D = 250uA	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16 V, V _{GS} = 0V			1	uA
Gate-to-source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250uA	0.4	0.62	1.00	V
Drain-to-source On-resistance	R _{DS(on)}	V _{GS} = 4.5V, I _D = 3.6A		27	36	mΩ
		V _{GS} = -2.5V, I _D = 2.8A		31	41	
		V _{GS} = 1.8V, I _D = 2.0A		36	47	
Forward Transconductance	g _{FS}	V _{DS} = 5 V, I _D = 3.6A		10		S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 10 V		1025		pF
Output Capacitance	C _{OSS}			125		
Reverse Transfer Capacitance	C _{RSS}			120		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 3.6A		12.1		nC
Threshold Gate Charge	Q _{G(TH)}			0.66		
Gate-to-Source Charge	Q _{GS}			1.0		
Gate-to-Drain Charge	Q _{GD}			3.3		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	td(ON)	V _{GS} = 4.5 V, V _{DS} = 6 V, I _D = 2.0A, R _G = 6 Ω		6.5		ns
Rise Time	tr			11.5		
Turn-Off Delay Time	td(OFF)			48		
Fall Time	tf			20		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} = 0 V, I _S = 1.5A	0.5	0.62	1.5	V